

## Zener Diode Chips for ESD Protection

### 1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge(ESD) protection application
- 1-2 This specification applies to P-Type silicon Zener diode chip Device NO:WT-Z106P-4-14

### 2. Structure:

- 2-1 Planar type: Silicon Diode
- 2-2 Electrodes:
  - Top side:Aluminum Alloy(Anode).
  - Back side:Gold Layer(Cathode).

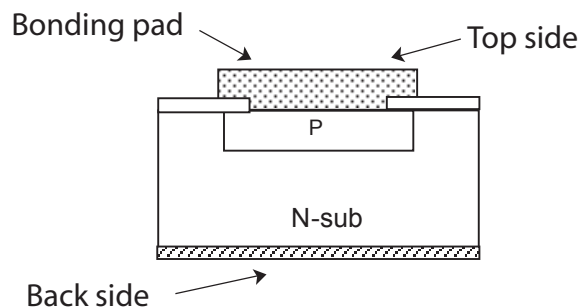
### 3. Size:

- 3-1. \*Chip size : 6.88 mils x 6.88 mils (175 $\mu$ m x 17.5 $\mu$ m ).
  - 3-2. Chip thickness : 3.3  $\pm$  0.6 mils (85  $\pm$  15 $\mu$ m ).
  - 3-3. Active area : 4.1 mils x 4.1 mils (105 $\mu$ m x 105 $\mu$ m).
  - 3-4. Bonding pad : 4.5 mils x 4.5 mils (115 $\mu$ m x 115 $\mu$ m) .
  - 3-5. Pattern drawing : Refer to the attached drawing.
- \* Including scribing line. The chip size is about 5.9mil(0.150mm) after dicing.

### 4. Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	V <sub>Z</sub>	I <sub>Z</sub> =5mA	12.5	-	15.5	V
Forward Voltage	V <sub>f</sub>	I <sub>F</sub> =20mA	-	-	1.2	v
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =10V	-	-	100	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0	-	-	KV

### 5. Drawing:



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